



SILERGY

Application Note: SQ29012

High Efficiency, 18V/12A Synchronous Step Down Regulator

Advanced Design Specification

General Description

The SQ29012 develops a high efficiency synchronous step-down DC/DC regulator capable of delivering 12A current. The device integrates high-side power switch and low-side synchronous rectifier with very low $R_{DS(ON)}$ to minimize the conduction loss. It provides accurate regulation for a variety of loads with an accurate $\pm 1\%$ voltage reference (V_{REF}) over $T_J = -40^\circ\text{C}$ to 125°C .

The SQ29012 operates over a wide input voltage range from 2.7V to 18V. The DC/DC regulator adopts the instant PWM architecture to achieve fast transient responses for high step down applications. Cycle-by-cycle current limit, hiccup over current protection and thermal shutdown protect the device during an over current condition

Ordering Information

SQ29012 □ (□ □) □
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 Temperature Code
 Package Code
 Optional Spec Code

Ordering Number	Package type	Note
SQ29012VDC	QFN3×4-19	

Applications

- Power Module
- Telecom and Networking Systems
- Servers
- LCD-TV/Net-TV/3DTV
- Set Top Box
- Notebook
- High Power AP

Features

- Wide Input Voltage Range:
 - 3.6V to 18V if VCC is Supplied by Internal LDO
 - 2.7V to 18V if VCC is Supplied by External 3.3V DC Source
- Low $R_{DS(ON)}$ for Internal Switches (Top/Bottom): 12.6m Ω /4.3m Ω
- 0.6V $\pm 1\%$ Voltage Reference Over Temperature Range ($T_J = -40^\circ\text{C}$ to 125°C)
- Adopt Constant-on-time Architecture and Frequency Lock Loop
- Instant PWM Architecture to Achieve Fast Transient Response.
- 600kHz, 800kHz and 1000kHz Switching Frequency Operation Selected by MODE Pin
- PFM/FCCM Light Load Operation Mode Selected by MODE pin.
- Programmable Bottom Valley Limit by ILMT pin
- Reliable Protection Mode: Auto-Recovery Mode for UVP, UVLO, OTP and OVP
- Cycle-by-cycle Valley Current Limit and Peak Current Limit
- Cycle-by-cycle Reverse Current Limit
- Internal Soft-start Limits the Inrush Current
- Programmable Soft-start Time by SS Pin
- Smooth Soft-start with Output Pre-biased Function
- Adjustable Input Voltage UVLO by EN Pin
- Power Good Indicator
- Differential Output Voltage Remote Sense
- Output Discharge Function
- Output Quick Discharging Mode
- RoHS Compliant and Halogen Free
- Compact Package: QFN3×4-19

Typical Application

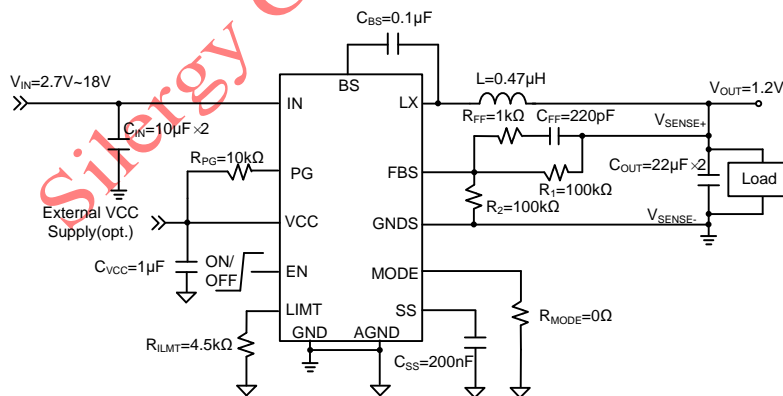


Figure1. Typical Application Circuit

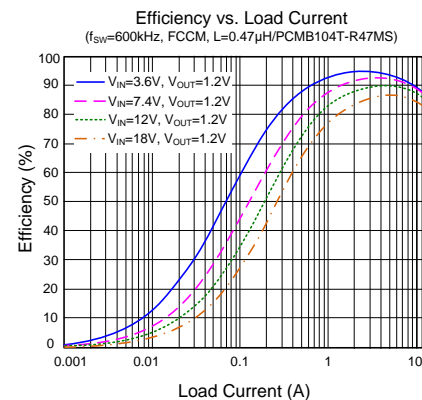
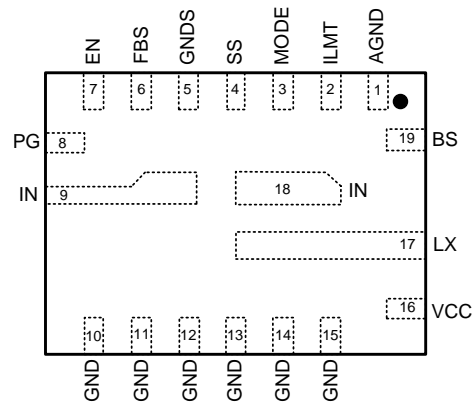


Figure2. Efficiency vs. Load Current



Pinout (top view)



(QFN3×4-19)

Top Mark: **DDD**xyz (Device code: **DDD**, *x*=year code, *y*=week code, *z*=lot number code)

Pin No	Pin Name	Pin Description
1	AGND	Analog ground.
2	ILMT	Bottom MOSFET current limit set pin. Connect a resistor to AGND to set the inductor valley current limit value.
3	MODE	Operation mode selection. Program MODE to select FCCM/PFM, and the operating switching frequency.
4	SS	External soft-start Voltage pin. Soft-start time can be adjusted by adding an appropriate external capacitor between this pin and AGND pin. IC actual soft-start time is determined by the slower ramp between internal SS voltage and external SS voltage.
5	GNDS	Remote sense negative input. Connect this pin directly to the negative side of the voltage sense point. Short to GND if remote sense is not used.
6	FBS	Remote sense positive input. Connect to the center point of resistor divider.
7	EN	Enable pin. Pull low to disable the device and pull high to enable the device. Can be used to set the input voltage on and off threshold (adjust UVLO) by using two additional resistors. Do not leave this pin floating.
8	PG	Power good Indicator. Open drain output when the output voltage is within 93.5% to 120% of regulation point.
9, 18	IN	Input pin. Decouple this pin to GND pin with at least a 20μF ceramic capacitor.
10, 11, 12, 13, 14, 15	GND	Power GND.
16	VCC	Internal 3.3V LDO output. Power supply for internal analog circuits and driving circuit. Decouple this pin to GND with at least one 1μF ceramic capacitor. Make one Kelvin connection from VCC capacitor negative plate to the AGND pin.
17	LX	Inductor pin. Connect this pin to the switching node of inductor.
19	BS	Boot-strap pin. Supply high side gate driver. Connect a 0.1 μF ceramic capacitor between the BS and the LX pin.



Block Diagram

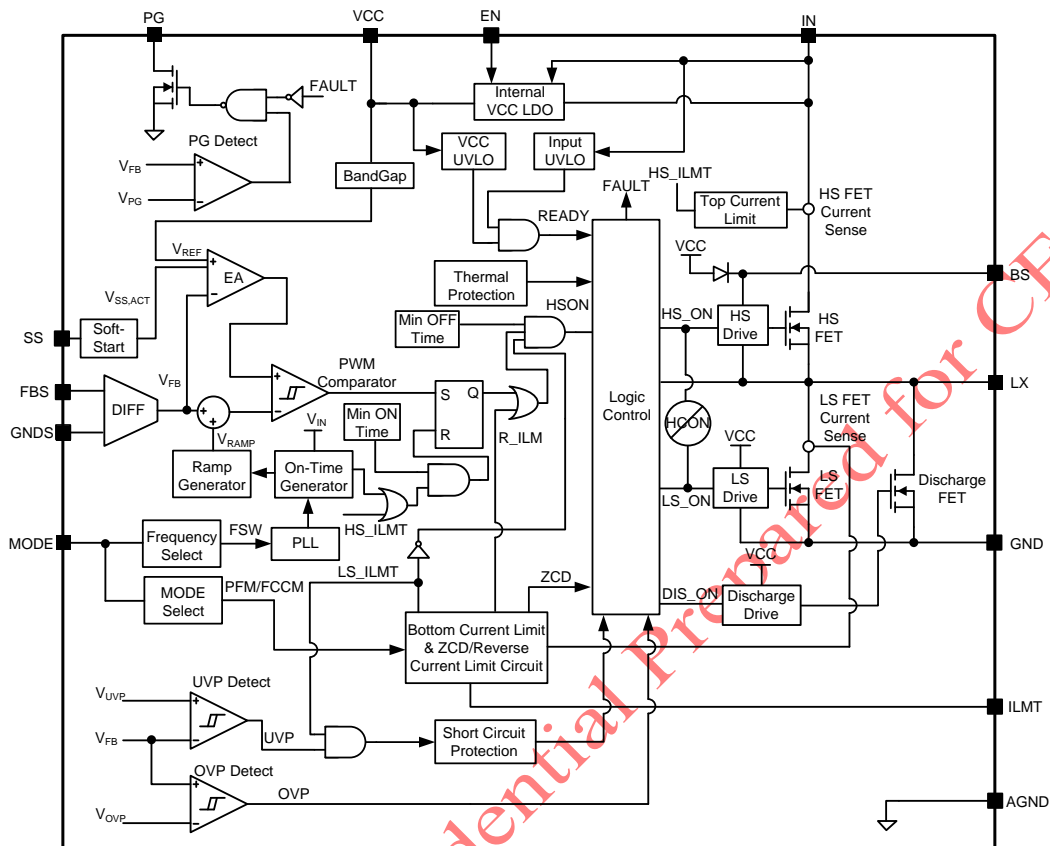


Figure3. Block Diagram

Absolute Maximum Ratings (Note 1)

Supply Input Voltage	-----	-0.3V to 19V
ILMT, EN, MODE, SS, LX Voltage	-----	-0.3V to $V_{IN}+0.3V$
Dynamic LX Voltage in 25ns Duration	-----	GND-5V to $V_{IN}+5V$
BS	-----	$V_{LX}-0.3V$ to $V_{LX}+4V$
FBS, GNDS, AGND, VCC, PG Voltage	-----	-0.3V to 4V
Maximum Power Dissipation, $P_{D, MAX}$ @ $T_A=25^\circ C$, QFN3×4-19	-----	4W
Package Thermal Resistance (Note2)		
θ_{JA}	-----	25 $^\circ C/W$
θ_{JC}	-----	5 $^\circ C/W$
Junction Temperature Range	-----	-40 $^\circ C$ to 150 $^\circ C$
Lead Temperature (Soldering, 10 sec.)	-----	260 $^\circ C$
Storage Temperature Range	-----	-65 $^\circ C$ to 150 $^\circ C$

Recommended Operating Conditions (Note 3)

Supply Input Voltage	-----	2.7V to 18V
Output Voltage	-----	0.6V to 5.5V
VCC Bias External Voltage	-----	3.12V to 3.6V
EN Supply Voltage	-----	0V to V_{IN}
Maximum Output Current	-----	12A
Maximum Output Current Limit	-----	14A
Maximum Inductor Peak Current	-----	16A
Junction Temperature Range	-----	-40 $^\circ C$ to 125 $^\circ C$



Electrical Characteristics

($V_{IN} = 12V$, $T_J = -40\text{ }^\circ\text{C}$ to $+125\text{ }^\circ\text{C}$. Typical values are at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified. The values are guaranteed by test, design or statistical correlation)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage Range	V_{IN}		2.7		18	V
Output Voltage Range	V_{OUT}		0.6		5.5	V
Input UVLO Rising Threshold	$V_{IN,UVLO}$		2.52	2.6	2.68	V
Input UVLO Hysteresis	$V_{IN,HYS}$			200		mV
VCC UVLO Rising Threshold	$V_{VCC,UVLO}$				2.5	V
VCC UVLO Hysteresis	$V_{VCC,HYS}$			100		mV
VCC Regulator Output Voltage	V_{CC}	$I_{VCC}=0\text{mA}$	3.1	3.25	3.4	V
VCC Load Regulation	$V_{CC,REG}$	$I_{VCC}=25\text{mA}$		1.8		% V_{CC}
Quiescent Current	I_Q	$V_{EN}=2V$, $V_{FBS} = 0.65V$, PFM mode, No Switching		650	850	μA
Shutdown Current	I_{SHDN}	$V_{EN}=0V$, $T_J=25\text{ }^\circ\text{C}$		3	5	μA
Feedback Reference Voltage	V_{REF}	$-40\text{ }^\circ\text{C} < T_J < 125\text{ }^\circ\text{C}$	0.594	0.600	0.606	V
Error Amplifier Offset	V_{OS}	(Note 4)	-3		3	mV
FBS Input Current	I_{FBS}	$V_{EN}=2V$, $V_{FBS} = 1V$	-50	0	50	nA
SS Charging Current	I_{SS1}	$V_{SS}=0V$		42		μA
SS Pull Down Current	I_{SS2}	$V_{SS}=1V$		42		mA
Minimum Soft-Start Time	$t_{SS,MIN}$	$C_{SS}=1\text{nF}$ (Note 4)		1		ms
Top FET $R_{DS(ON)}$	$R_{DS(ON)1}$	$V_{BS-LX} = 3.3V$, $T_J=25\text{ }^\circ\text{C}$		12.6	18.9	$\text{m}\Omega$
Bottom FET $R_{DS(ON)}$	$R_{DS(ON)2}$	$V_{CC} = 3.3V$, $T_J=25\text{ }^\circ\text{C}$		4.3	6.5	$\text{m}\Omega$
Top FET Leakage	$I_{TOP, LKG}$	$V_{EN}=0V$, $V_{DS}=12V$		0.01	4	μA
Bottom FET Leakage	$I_{BOT, LKG}$	$V_{EN}=0V$, $V_{DS}=12V$		0.03	28	μA
EN Rising Threshold	$V_{EN,R}$		1.16	1.21	1.26	V
EN Threshold Hysteresis	$V_{EN,HYS}$			0.23		V
EN Input Current	I_{EN}	$V_{EN}=2V$		0		μA
Discharge FET Resistance	R_{DIS}			60		Ω
Top FET Current Limit	$I_{LMT, TOP}$		11.6	14.3	17	A
Bottom FET Reverse Current Limit	$I_{LMT, RVS}$		3	4.5	6	A
Reverse Current Limit Blank Time	$t_{RCL, BLK}$	(Note 4)	40	60		ns
ILMT Pin Output Voltage	V_{ILMT}		1.15	1.2	1.25	V
I_{LMT} to $I_{LMT, BOT}$ Ratio	$I_{LMT}/I_{LMT, BOT}$	$I_{LMT, BOT} > 5A$	18	20	22	$\mu\text{A}/\text{A}$
Output OVP Threshold	V_{OVP}		110	120	130	% V_{REF}
Output UVP Threshold	V_{UVP}		45	50	55	% V_{REF}
Output UVP Delay	$t_{UVP, DLY}$	(Note 4)		20		μs
UVP/OCP Hiccup ON Time	$t_{HICUP, ON}$	$C_{SS}=1\text{nF}$ (Note 4)		3		ms



UVP/OCF Hiccup OFF Time	$t_{HICcup,OFF}$	$C_{SS}=1nF$ (Note 4)		15		ms
Power Good Threshold	V_{PG}	V_{FBS} falling, PG high to low	76	79	82	% V_{REF}
		V_{FBS} rising, PG low to high	90	93.5	97	% V_{REF}
		V_{FBS} rising, PG high to low	110	120	130	% V_{REF}
		V_{FBS} falling, PG low to high	100	103.5	107	% V_{REF}
Power Good Leakage Current	$I_{PG,LKG}$	PG voltage is 3.3V		3	5	μA
Power Good Delay	$t_{PG,R}$	V_{FBS} falling, PG low to high (Note 4)		0.8		ms
	$t_{PG,F}$	V_{FBS} rising, PG high to low (Note 4)		20		μs
Power Good Sink Current Capability	$V_{PG,LOW}$	$V_{EN} = 2V, V_{FBS} = 0V, I_{PG}=10mA$			0.4	V
Power Good Output Low Voltage	$V_{PG,L}$	$V_{IN}=0V$, Pull PG to 3.3V through 100k Ω Resistor		550	750	mV
		$V_{IN}=0V$, Pull PG to 3.3V through 10k Ω Resistor		660	850	mV
Min ON Time	$t_{ON,MIN}$	$I_{OUT}=3A$ (Note 4)		55		ns
Min OFF Time	$t_{OFF,MIN}$	$I_{OUT}=3A$ (Note 4)		150		ns
Switching Frequency	f_{SW}	$R_{MODE}=0\Omega, I_{OUT}=0A, FCCM, V_{OUT}=1V, T_J=25^\circ C$	500	600	700	kHz
		$R_{MODE}=30.1k\Omega, I_{OUT}=0A, FCCM, V_{OUT}=1V, T_J=25^\circ C$	710	800	890	kHz
		$R_{MODE}=60.4k\Omega, I_{OUT}=0A, FCCM, V_{OUT}=1V, T_J=25^\circ C$	900	1000	1100	kHz
Thermal Shutdown Temperature	T_{SD}	T_J rising (Note 4)	140	160		$^\circ C$
Thermal Shutdown Hysteresis	T_{HYS}	(Note 4)		30		$^\circ C$

Note 1: Stresses beyond the “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note2: Package thermal resistance is measured in the natural convection at $T_A=25^\circ C$ on a 8.5cm \times 8.5cm size four-layer Silergy Evaluation Board.

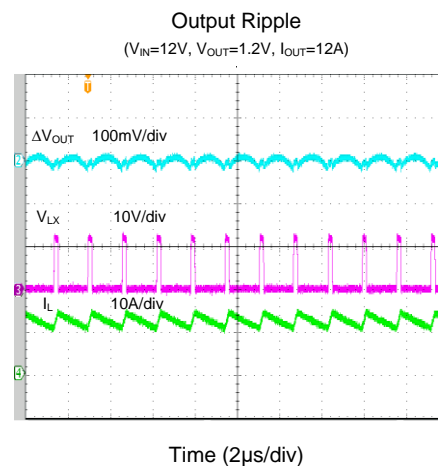
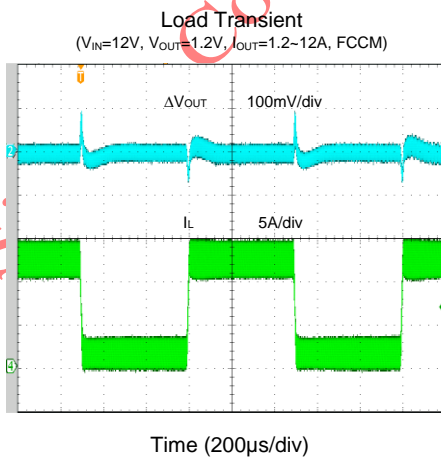
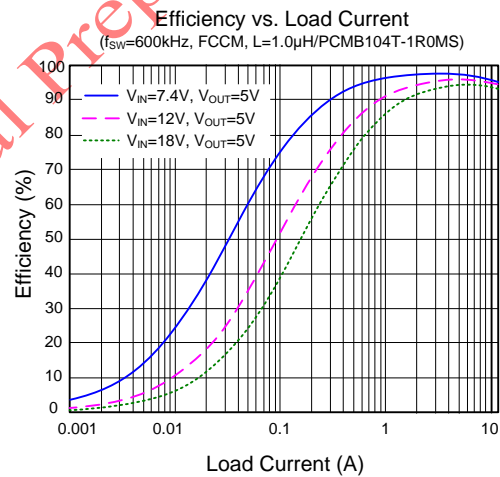
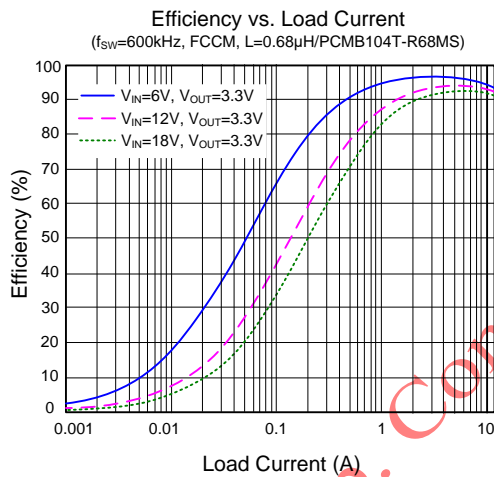
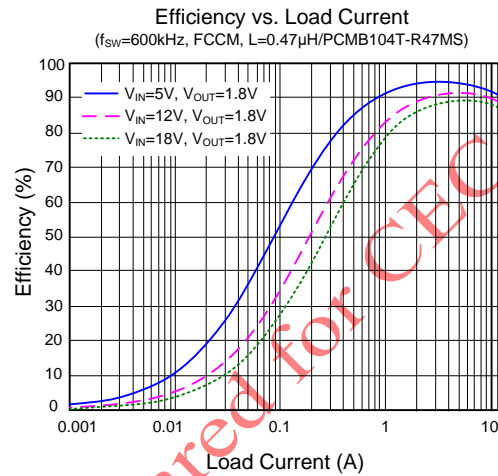
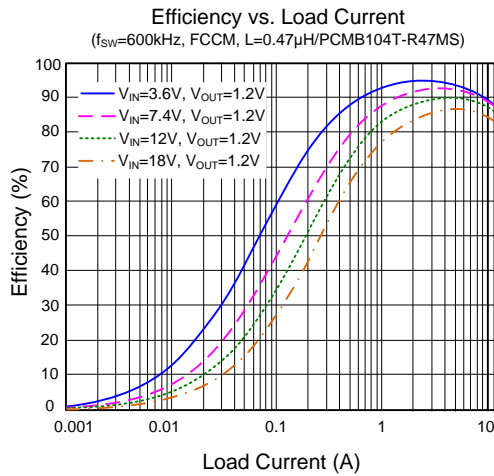
Note 3: The device is not guaranteed to function outside its operating conditions.

Note 4: Guaranteed by design.

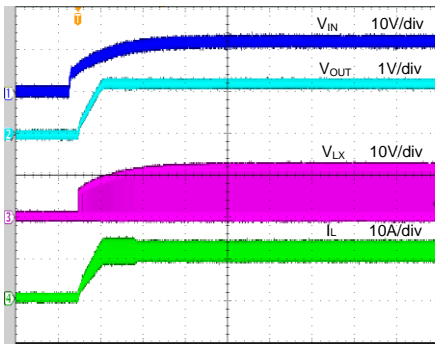


Typical Performance Characteristics

($T_A=25^{\circ}\text{C}$, $V_{IN}=12\text{V}$, $V_{OUT}=1.2\text{V}$, $L=0.47\mu\text{H}$, $C_{OUT}=44\mu\text{F}$, $f_{SW}=600\text{kHz}$, $R_{ILMT}=4.5\text{k}\Omega$, $C_{SS}=0.2\mu\text{F}$, unless otherwise noted)

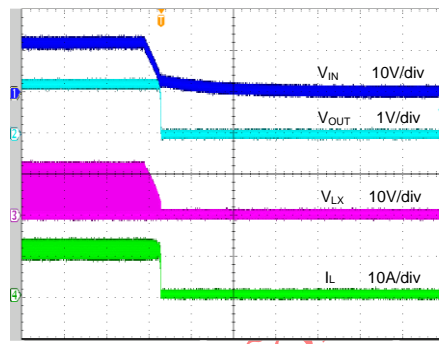


Startup from V_{IN}
 $(V_{IN}=12V, V_{OUT}=1.2V, I_{OUT}=12A)$



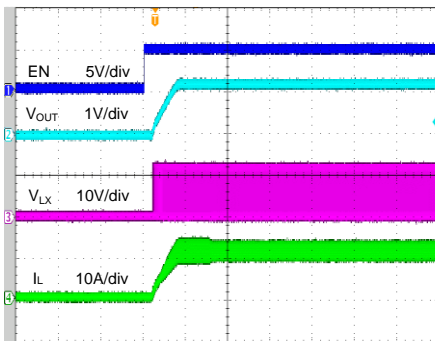
Time (4ms/div)

Shutdown from V_{IN}
 $(V_{IN}=12V, V_{OUT}=1.2V, I_{OUT}=12A)$



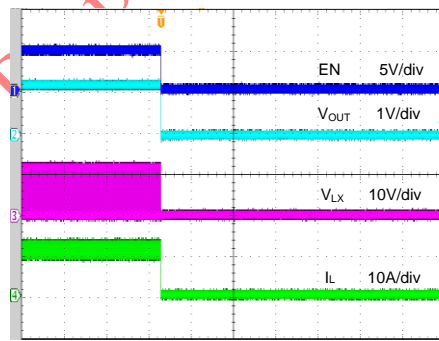
Time (2ms/div)

Startup from EN
 $(V_{IN}=12V, V_{OUT}=1.2V, I_{OUT}=12A)$



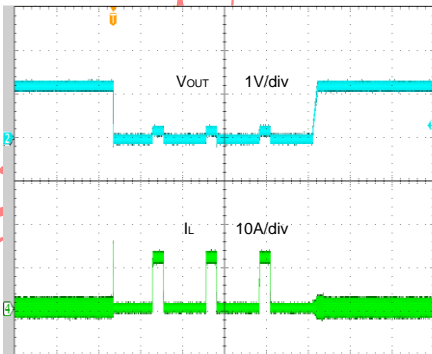
Time (4ms/div)

Shutdown from EN
 $(V_{IN}=12V, V_{OUT}=1.2V, I_{OUT}=12A)$



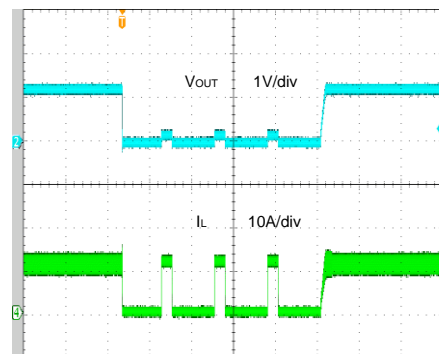
Time (4ms/div)

Short Circuit Protection
 $(V_{IN}=12V, V_{OUT}=1.2V, I_{OUT}=0A\text{-short}, R_{LIMIT}=4.5k\Omega, FCCM)$



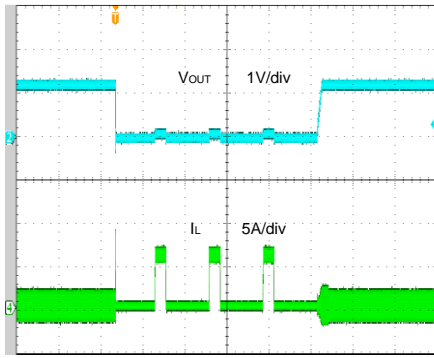
Time (20ms/div)

Short Circuit Protection
 $(V_{IN}=12V, V_{OUT}=1.2V, I_{OUT}=12A\text{-short}, R_{LIMIT}=4.5k\Omega, FCCM)$



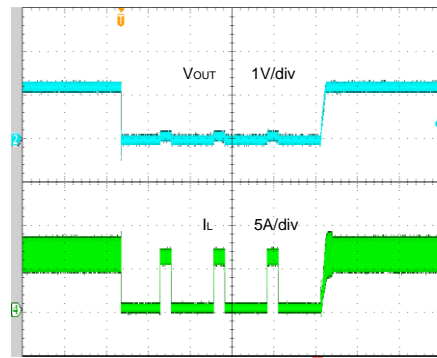
Time (20ms/div)

Short Circuit Protection
 ($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=0A$ -short, $R_{LIMIT}=10k\Omega$, FCCM)



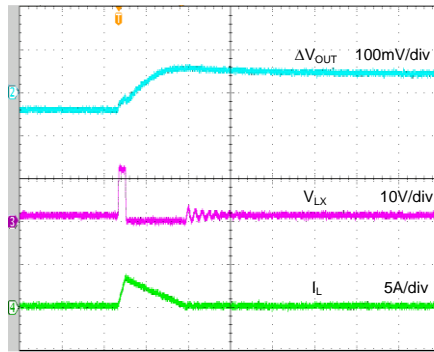
Time (20ms/div)

Short Circuit Protection
 ($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=6A$ -short, $R_{LIMIT}=10k\Omega$, FCCM)



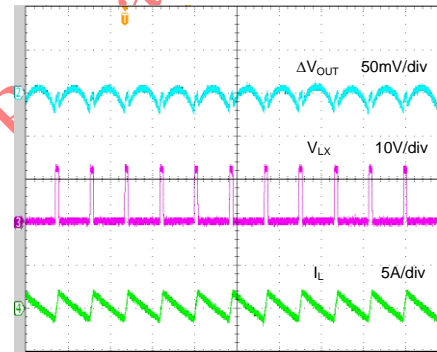
Time (20ms/div)

Output Ripple
 ($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=0A$, PFM)



Time (1 μ s/div)

Output Ripple
 ($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=0A$, FCCM)



Time (2 μ s/div)

Silergy Corp. Confidential



Detailed Description

General Features

Constant-on-time Architecture and Frequency

Lock Loop (FLL)

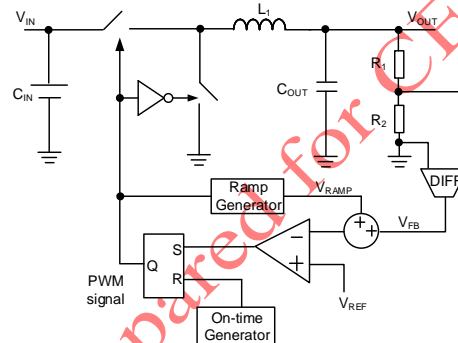
Fundamental to any constant-on-time (COT) architecture is the one-shot circuit or on-time generator, which determines how long to turn on the high-side power switch. Each on-time (t_{ON}) is a “fixed” period internally calculated to operate the step down regulator at the desired switching frequency considering the input and output voltage ration, $t_{ON}=(V_{OUT}/V_{IN})\times(1/f_{SW})$. For example, considering that a hypothetical converter targets 1.2V output from a 12V input at 600kHz, the target on-time is $(1.2V/12V)\times(1/600kHz)=167ns$. Each t_{ON} pulse is triggered by the feedback comparator when the output voltage as measured at FB drops below the target value. After one t_{ON} period, a minimum off-time ($t_{OFF,MIN}$) is imposed before any further switching is initiated, even if the output voltage is less than the target. This approach avoids the making any switching decisions during the noisy periods just after switching events and while the switching node (LX) is rapidly rising or falling.

In a COT architecture, there is no fixed clock, so the high-side power switch can turn on almost immediately after a load transient and subsequent switching pulses can be quickly initiated, ramping the inductor current up to meet load requirements with minimal delays. Traditional current mode or voltage mode control methods must simultaneously monitor the feedback voltage, current feedback and internal ramps and compensation signals to determine when to turn off the high-side power switch and turn on the low-side synchronous rectifier. Considering these small signals in a switching environment are difficult to be noise-free after switching large currents, making those architectures difficult to apply in noisy environments and at low duty cycles.

On one hand, once the on-time calculated by the constant-on-time architecture has one deviation from the accurate on-time value, especially in the case of small duty cycle operation, the actual switching frequency will deviate from the setting value largely. On the other hand, when the load is close to full load, the duty cycle loss will also cause switching frequency deviation. In order to maintain the switching frequency constant relatively under different application conditions, the constant-on-time architecture needs one frequency lock loop (FLL). In the PLL, the reference frequency is one fixed clock, keeps the same as the setting frequency, and the switching frequency is compared with it cycle by

cycle. This loop will adjust the actual on-time, let the switching frequency follow the reference frequency until there is no deviation between them. This FLL function is disabled during soft-start process and discontinuous current mode (DCM) condition. Before soft-start process is done, the CCM switching frequency is equal to one initial frequency, which is a little bit less than the reference frequency.

Instant-PWM Operation



Silergy’s instant-PWM control method adds several proprietary improvements to the traditional COT architecture. Whereas most legacy based on COT implementations require a dedicated connection to the output voltage terminal to calculate the t_{ON} duration, instant-PWM control method derives this signal internally. Another improvement optimizes operation with low ESR ceramic output capacitors. In many applications it is desirable to utilize very low ESR ceramic output capacitors, but legacy COT regulators may become unstable in these cases because the beneficial ramp signal that results from the inductor current flowing into the output capacitor maybe become too small to maintain smooth operation. For this reason, instant-PWM synthesizes a virtual replica of this signal internally. This internal virtual ramp and the feedback voltage are combined and compared to the reference voltage. When the sum is lower than the reference voltage, the t_{ON} pulse is triggered as long as the minimum t_{OFF} has been satisfied and the inductor current as measured in the low-side synchronous rectifier is lower than the bottom FET current limit. As the t_{ON} pulse is triggered, the low-side synchronous rectifier turns off and the high-side power switch turns on. Then the inductor current ramps up linearly during the t_{ON} period. At the conclusion of the t_{ON} period, the high-side power switch turns off, the low-side synchronous rectifier turns on and the inductor current ramps down linearly. This action also initiates the minimum t_{OFF} timer to ensure sufficient time for stabilizing any transient conditions and settling the feedback comparator before the next cycle is



initiated. This minimum t_{OFF} is relatively short so that during high speed load transient t_{ON} can be retriggered with minimal delay, allowing the inductor current to ramp quickly to provide sufficient energy to the load side.

In order to avoid shoot-through, a dead time (t_{DEAD}) is generated internally between the high-side power switch off and the low-side synchronous rectifier on period or the low-side synchronous rectifier off and the high-side power switch on period.

Light Load Operation Mode and Switching

Frequency Selection

PFM or FCCM light load operation mode and switching frequency are both selected by MODE pin. Once the light load operation mode and switching frequency is selected after VCC set up, then it will be locked unless the device shuts down. See the following table.

MODE	Light-Load Mode	Switching Frequency
VCC	PFM	600kHz
240k Ω ($\pm 20\%$) to GND	PFM	800kHz
120k Ω ($\pm 20\%$) to GND	PFM	1000kHz
GND	FCCM	600kHz
30k Ω ($\pm 20\%$) to GND	FCCM	800kHz
60k Ω ($\pm 20\%$) to GND	FCCM	1000kHz

If PFM light load operation is selected, under light load conditions, typically $I_{OUT} < 1/2 \times \Delta I_L$, the current through the low-side synchronous rectifier will ramp to near zero before the next t_{ON} time. When this occurs, the low-side synchronous rectifier turns off, preventing recirculation current that can seriously reduce efficiency under these light load conditions. As load current is further reduced, and the combined feedback and ramp signals remain much greater than the reference voltage, the instant-PWM control loop will not trigger another t_{ON} until needed, so the apparent operating switching frequency will correspondingly drop, further enhancing efficiency. The switching frequency can be lower than audible frequency area under deep light load or null load conditions. Continuous conduction mode (CCM) resumes smoothly as soon as the load current increases sufficiently for the inductor current to remain above zero at the time of the next t_{ON} cycle. The device enters CCM once the load current exceeds the critical level. After that, the switching

frequency stays fairly constant over the output current range. The critical level of the load current is determined with

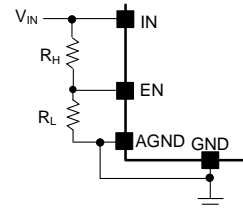
$$I_{OUT_CTL} = \frac{\Delta I_L}{2} = \frac{V_{OUT} \times (1-D)}{2 \times f_{SW} \times L_1}$$

If FCCM light load operation is selected, under light load conditions, the low-side synchronous rectifier still turns on even when the inductor current crosses zero. Current flow will continue until the next t_{ON} cycle. The device always operates under continuous conditions mode and keeps fairly constant switching frequency over all the output current range.

Input Under Voltage Lock-out (UVLO)

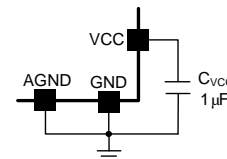
To prevent operation before all internal circuitry is ready and to ensure that the power and synchronous rectifier switches can be sufficiently enhanced, the instant-PWM incorporates one input under-voltage lockout protections. The device remains in a low current state and all switching actions are inhibited until V_{IN} exceeds their own UVLO (rising) threshold. At that time, if EN is enabled, the device will start-up by initiating a soft-start ramp. If V_{IN} falls below $V_{IN,UVLO}$ less than the input UVLO hysteresis, switching actions will again be suppressed.

If the input UVLO threshold is low for some high input UVLO threshold requirement applications, use EN to adjust the input UVLO by adopting two external divided resistors.



VCC Linear Regulator and VCC UVLO

The SQ29012 integrates one high performance, low drop-out linear regulator 3.3V VCC, supplied by input voltage, which can power the internal gate drivers, PWM logic, analog circuitry and other blocks. Connect a 1 μF low ESR ceramic capacitor from VCC to GND.



Like input UVLO design, VCC has also one UVLO protection. When the VCC voltage is lower than VCC UVLO rising threshold for one VCC UVLO



hysteresis, the device will shut down to ensure all internal circuitry logic is right and the power and synchronous rectifier switches can be sufficiently enhanced.

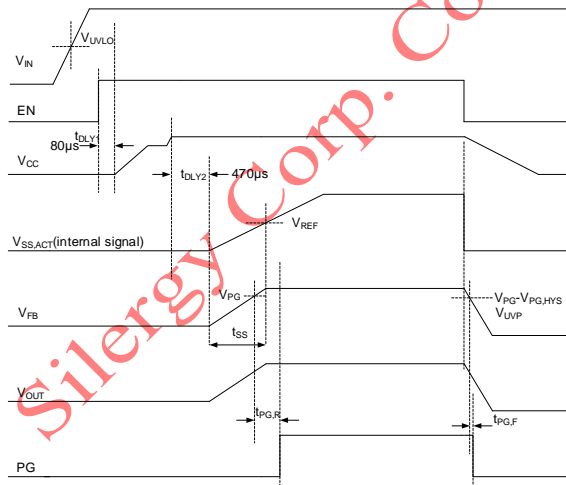
Enable Control

The EN input is a high-voltage capable input with logic-compatible threshold. The comparator design scheme makes the EN rising threshold accurate comparatively. When EN voltage rises to ~0.8V, VCC works so that the EN comparator has source supply. When EN is driven above 1.21V normal device operation will be enabled, and the switching node pulse appear. When EN voltage falls lower than EN rising threshold for one hysteresis, the switching node pulse is inhibited. When EN voltage is driven < 0.4V the VCC will be shut down, reducing input current to < 5 μA (Normal temperature).

It is not recommended to connect EN and IN directly. A resistor in a range of 1kΩ to 1MΩ should be used if EN is pulled high by IN.

Startup and Shutdown

The SQ29012 incorporates an internal soft-start circuit to smoothly ramp the output to the desired voltage whenever the device is enabled. Internally, the soft-start circuit clamps the output at a low voltage and then allows the output to rise to the desired voltage over approximately one soft-start time, which avoids high current flow and transients during startup. The startup and shutdown sequence is shown below.



After the input voltage exceeds its own UVLO (rising) threshold, VCC is turned on after EN is enabled for a delay time t_{DLY1}, the buck regulator is turned on after another delay time t_{DLY2} after VCC voltage is set up. When the output voltage is 93.5% of

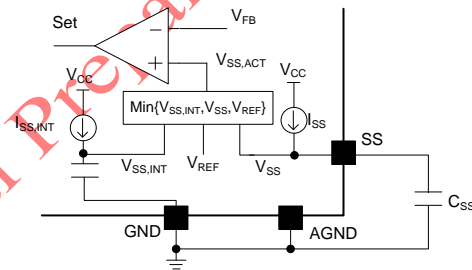
the regulation point, PG becomes high-impedance after a delay time t_{PG,R}.

Programmable Soft-start Time and On-time Pre-bias Function

The soft-start time can be programmable by SS pin. Connect one capacitor between SS pin and AGND pin to program the soft-start time. The actual soft-start time is determined by the slower rising slew rate of the external SS voltage V_{SS} and internal SS voltage V_{SS,INT}. The soft-start time equation is:

$$t_{SS}(\text{ms}) = \frac{C_{SS}(\text{nF}) \times V_{REF}}{I_{SS}(\mu\text{A})}$$

The typical value of SS charging current I_{SS} is 42μA. To guarantee the programmable soft-start time is not too short when using smaller SS capacitor, there is one minimum soft-start time limitation, the minimum soft-start time is 1ms.



When under voltage protection (UVP) occurs, the hic-cup on time and hiccup off time is also determined by the slower SS voltage slew rate, but the time ratio keeps still 1:5.

If the output is pre-biased to a certain voltage before start-up, the device disables the switching of both the high-side power switch and the low-side synchronous rectifier until the voltage on the internal soft start circuit voltage V_{SS,ACT} exceeds the sensed output voltage at the FB node. Before the switching node pulse occurs, the switching node voltage is sampled to internal on-time generator circuit to make on-time pre-bias, in order to the first on-time will be matched with the current pre-bias output voltage.

What is worth mentioning, in the output voltage pre-biased scenario, if the BS-LX voltage is lower than 1.8V, the low-side synchronous rectifier turns on to allow the BS voltage to be charged by VCC. The low-side synchronous rectifier turns on just for one very narrow pulse, so the drop in the pre-biased output level is negligible.



Differential Output Voltage Remote Sense Function

The device supports differential remote output voltage sense function. The dedicated GNDS pin helps provide the remote GND voltage sense, cooperating with remote OUT voltage sense in order to prevent the remote load side’s voltage decrease largely even the load current is high up to 12A. The pair of the remote sense trace should be kept in low impedance to achieve the best performance.

Output Discharge Function

The SQ29012 discharges the output voltage when the converter shuts down from V_{IN} or EN, or thermal shutdown, so that output voltage can be discharged in a minimal time, even load current is zero. The discharge FET in parallel with the low-side synchronous rectifier turns on after the low-side synchronous rectifier turns off when shut down logic is triggered. The output discharge FET $R_{DS(ON)}$ is typically 60Ω under room temperature. Note that the discharge FET is not active beyond these shutdown conditions.

Output Quick Discharging Mode (OODM)

When the device works under PFM light load operation mode, if the FB voltage is higher than OVP threshold for more than 20μs, the output quick discharging mode will be activated. Like FCCM work state, the zero-cross point detect is blanked and the low-side synchronous rectifier turns on until the reverse current limit point is triggered, so that the output voltage discharges as quickly as possible. As the output voltage falls close to the setting level, the inductor current will rise to one positive value, once the low-side synchronous rectifier detects its current is positive, then zero-cross point recovers and the output quick discharge mode quits, the low-side synchronous rectifier turns off once inductor current triggers zero-cross point.

Buck Output Power Good Indicator

The Buck power good indicator is an open drain output controlled by a window comparator connected to the feedback signal. If V_{FB} is greater than $V_{PG,R}$ and less than V_{OVP} for at least the power good delay time, (low to high), PG will be high-impedance.

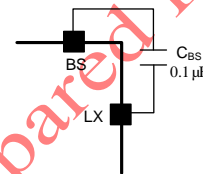
PG should be connected to V_{IN} or another voltage source through a resistor (e.g. 10kΩ~100kΩ). After V_{IN} exceeds its own UVLO (rising) threshold, the PG FET is turned on so that PG is pulled to GND before output voltage is ready. After feedback voltage V_{FB} reaches $V_{PG,R}$, PG is pulled high (after a delay time within 800μs). When V_{FB} drops to $V_{PG,F}$, or rises to

V_{OVP} for one OVP delay time, PG is pulled low (after a delay time within 20μs).

PG circuit adopts special design, when the PG connects with external power source through 10kΩ~100kΩ, even the input voltage is zero, the PG voltage keeps one output low voltage level.

External Bootstrap Capacitor Connection

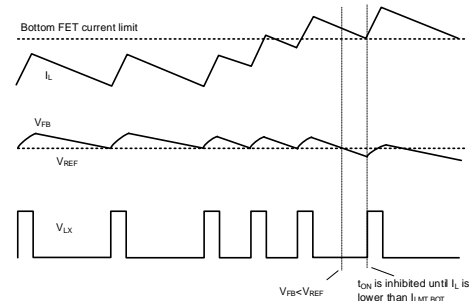
This device integrates a floating power supply for the gate driver that operates the high-side power switch. Proper operation requires a 0.1μF low ESR ceramic capacitor to be connected between BS and LX. This bootstrap capacitor provides the gate driver supply voltage for the high-side N-channel MOSFET power switch.



Fault Protection Modes

Programmable Valley Current Limit Protection

Instant-PWM incorporates a cycle-by-cycle “valley” current limit. Inductor current is measured in the low-side synchronous rectifier when it turns on and as the inductor current ramps down. If the current exceeds the bottom FET current limit, t_{ON} is inhibited until the current returns back to safe levels.



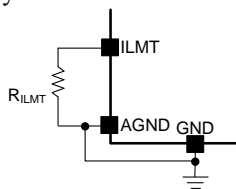
The OCP limits the inductor current but the device does not latch off. Under an over current condition, the current to the load exceeds the current to the output capacitor, thus the output voltage tends to fall off. Eventually, it will end up with crossing the under voltage protection (UVP) threshold and the device will latch off. On the other hand, over temperature protection may also be triggered under an over-current condition and the device will latch off. Overall, the device tends to trigger UVP or OTP latch off protection under an over current condition and OCP itself is not latch off protection.



The valley current limit point can be programmable by ILMT pin. Connect one resistor from ILMT pin to the AGND pin to program valley current limit point. The ILMT output voltage is constant, the ILMT resistor current is sensed by the device, comparing with low-side synchronous rectifier current mirror value. If the mirror current is larger than the ILMT resistor current, the device works under valley current limit state and t_{ON} is inhibited. The valley current limit point equation is

$$I_{BOT,LMT} = \frac{V_{ILMT}}{G_{MIRROR} \times R_{ILMT} (\Omega)}$$

Where, ILMT output voltage V_{ILMT} is 1.2V, the low-side synchronous rectifier mirror ratio G_{MIRROR} is 20 μ A/A typically.



Peak Current Limit Protection

The device also features cycle-by-cycle “peak” current limit (top FET current limit). During t_{ON} time, the high-side power switch current is monitored. If the monitored current exceeds the top FET current limit, the high-side power switch is turned off, the low-side synchronous rectifier is turned on and then t_{ON} is inhibited. t_{ON} can be not inhibited any more once low-side synchronous rectifier current is lower than the bottom FET current limit value. Peak current limit protection has one blank time, at the initial on-time, high-side power switch current sample is disabled to make sampling noise shielding. Peak current limit protection priority is lower than minimum on-time.

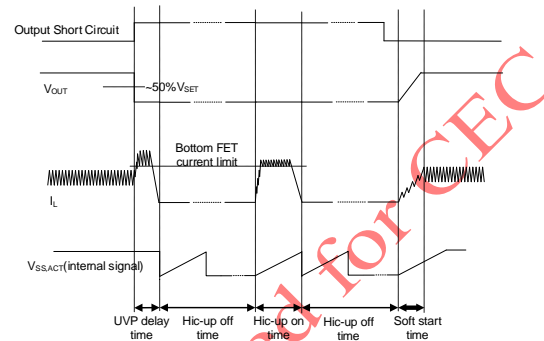
Reverse Current Limit Protection

The device also features cycle-by-cycle “reverse” current limit. When the device works under FCCM or PFM OQDM operation, the low-side synchronous rectifier current is monitored, if the current is lower than reverse current limit, the low-side synchronous rectifier is turned off, the high-side power switch is turned on. At the initial off-time, low-side synchronous rectifier current sample is disabled to make sampling noise shielding. The reverse current limit blank time is typical 60ns.

Output Under Voltage Protection (UVP)

If $V_{OUT} < \sim 50\%$ of the set point for approximately 20 μ s occurring when the output short circuit or the load current is much heavier than the maximum current capacity, the output under voltage protection

(UVP) will be triggered, and the device will enter into hic-cup protection mode. The minimum hic-cup on time is 3ms, and the minimum hic-cup off time is 15ms. If the output fault conditions are removed, the device will go back to normal operation in the nearest hic-cup on time.



Output Over Voltage Protection (OVP)

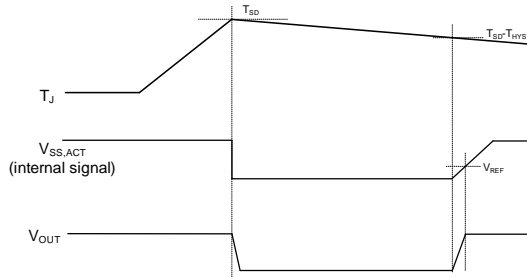
This device includes output over voltage protection (OVP). If the output voltage rises above the feedback regulation level, the high-side power switch naturally remains off and different actions are adopted in different operation mode.

When operating in PFM light load mode, if the output voltage remains higher than setting level but lower than OVP level, the low-side synchronous rectifier remains on until the inductor current reaches zero and the switching actions are suppressed. The switching actions will be recovered once the combined feedback and ramp signals become lower than the reference voltage. If the output voltage remains higher than OVP level for more than one OVP delay time, OQDM is activated.

When operating in FCCM light load mode, if the output voltage remains high, the reverse current limit will be triggered and inductor current average value becomes negative, trying to make output voltage lower. False OVP may happen under light load condition if the inductance is chosen too small and reverse current limit is triggered.

Over Temperature Protection (OTP)

Instant-PWM includes over temperature protection (OTP) circuitry to prevent overheating due to excessive power dissipation. This will shut down the device when the junction temperature exceeds 160 $^{\circ}$ C. Once the junction temperature cools down by approximately 30 $^{\circ}$ C, the device will resume normal operation after a complete soft-start cycle. For continuous operation, provide adequate cooling so that the junction temperature does not exceed the OTP threshold.

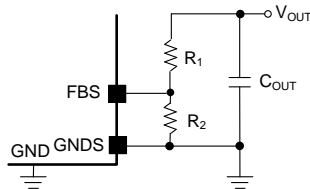


Design Procedure

Feedback Resistor Selection

Choose R_1 and R_2 to program the proper output voltage. To minimize the power consumption under light loads, it is desirable to choose large resistance values for both R_1 and R_2 . A value of between $10k\Omega$ and $1M\Omega$ is strongly recommended for both resistors. If V_{SET} is 1.2V, $R_1=100k\Omega$ is chosen, then using following equation, R_2 can be calculated to be $100k\Omega$.

$$R_2 = \frac{0.6V}{V_{SET} - 0.6V} \times R_1$$



Input Capacitor Selection

Input filter capacitors are needed to reduce the ripple voltage on the input, to filter the switched current drawn from the input supply and to reduce potential EMI. When selecting an input capacitor, be sure to select a voltage rating at least 20% greater than the maximum voltage of the input supply and a temperature rating above the system requirements. X5R or X7R series ceramic capacitors are most often selected due to their small size, low cost, surge current capability and high RMS current ratings over a wide temperature and voltage range. However, systems that are powered by a wall adapter or other long and therefore inductive cabling may be susceptible to significant inductive ringing at the input to the device. In these cases, consider adding some bulk capacitance like electrolytic, tantalum or polymer type capacitors. Using a combination of bulk capacitors (to reduce overshoot or ringing) in parallel with ceramic capacitors (to meet the RMS current requirements) is helpful in these cases.

Consider the RMS current rating of the input capacitor, paralleling additional capacitors if required to meet the calculated RMS ripple current,

$$I_{CIN_RMS} = I_{OUT} \times \sqrt{D \times (1-D)}$$

The worst-case condition occurs at $D = 0.5$, then

$$I_{CIN_RMS_MAX} = \frac{I_{OUT}}{2}$$

For simplification, choose an input capacitor with an RMS current rating greater than half of the maximum load current.

On the other hand, the input capacitor value determines the input voltage ripple of the converter. If there is an input voltage ripple requirement in the system, choose an appropriate input capacitor that meets the specification.

Given the very low ESR and ESL of ceramic capacitors, the input voltage ripple can be estimated by

$$V_{CIN_RIPPLE_CAP} = \frac{I_{OUT}}{f_{SW} \times C_{IN}} \times D \times (1-D)$$

The worst-case condition occurs at $D = 0.5$, then

$$V_{CIN_RIPPLE_CAP_MAX} = \frac{I_{OUT}}{4 \times f_{SW} \times C_{IN}}$$

The capacitance value is less important than the RMS current rating. In most applications two $22\mu F$ X5R capacitors is sufficient. Take care to locate the ceramic input capacitor as close to the device IN and GND pin as possible.

Inductor Selection

The inductor is necessary to supply constant current to the output load while being driven by the switched input voltage.

Instant-PWM operates well over a wide range of inductor values. This flexibility allows for optimization to find the best trade-off of efficiency, cost and size for a particular application. Selecting a low inductor value will help reduce size and cost and enhance transient response, but will increase peak inductor ripple current, reducing efficiency and increasing output voltage ripple. The low DC resistance (DCR) of these low value inductors may help reduce DC losses and increase efficiency. On the other hand, higher inductor values tend to have higher DCR and will slow transient response.

A reasonable compromise between size, efficiency, and transient response can be determined by selecting a ripple current (ΔI_L) about 20% ~ 50% of the desired full output load current. Start calculating the approximate inductor value by selecting the input and output voltages, the operating frequency (f_{SW}), the maximum output current (I_{OUT_MAX}) and estimating a ΔI_L as some percentage of that current.



$$L_1 = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times \Delta I_L}$$

Use this inductance value to determine the actual inductor ripple current (ΔI_L) and required peak current inductor current $I_{L,PEAK}$.

$$\Delta I_L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times L_1}$$

And $I_{L,PEAK} = I_{OUT,MAX} + \Delta I_L/2$

Select an inductor with a saturation current and thermal rating in excess of $I_{L,PEAK}$.

If FCCM light load operation is selected, make sure the inductor value is high enough to avoid reverse current limit is been triggered just under steady state if the load current is zero.

For highest efficiency, select an inductor with a low DCR that meets the inductance, size and cost targets. Low loss ferrite materials should be considered.

Inductor Design Example

Consider a typical design for a device providing $1.2V_{OUT}$ at $12A$ from $12V_{IN}$, operating at $600kHz$ and using target inductor ripple current (ΔI_L) of 50% or 6A. Determine the approximate inductance value at first:

$$L_1 = \frac{1.2V \times (12V - 1.2V)}{12V \times 600kHz \times 6A} = 0.3\mu H$$

Next, select the nearest standard inductance value, in this case $0.33\mu H$, and calculate the resulting inductor ripple current (ΔI_L):

$$\Delta I_L = \frac{1.2V \times (12V - 1.2V)}{12V \times 600kHz \times 0.33\mu H} = 5.45A$$

$$I_{L,PEAK} = 12A + 5.45A/2 = 14.725A$$

The resulting 5.45A ripple current is $5.45A/12A$ is ~45.4%, well within the 20% ~ 50% target.

$$I_{L,PEAK,RVS} = 5.45A/2 = 2.725A < I_{LIM,RVS}$$

Finally, select an available inductor with a saturation current higher than the resulting $I_{L,PEAK}$ of 14.725A.

Output Capacitor Selection

Instant-PWM provides excellent performance with a wide variety of output capacitor types. Ceramic and POS types are most often selected due to their small size and low cost. Total capacitance is determined by the transient response and output voltage ripple requirements of the system.

Output Ripple

Output voltage ripple at the switching frequency is caused by the inductor current ripple (ΔI_L) on the output capacitors ESR (ESR ripple) as well as the stored charge (capacitive ripple). When considering total ripple, both should be considered.

$$V_{RIPPLE,ESR} = \Delta I_L \times ESR$$

$$V_{RIPPLE,CAP} = \frac{\Delta I_L}{8 \times C_{OUT} \times f_{SW}}$$

Consider a typical application with $\Delta I_L = 5.45A$ using two $22\mu F$ ceramic capacitors, each with an ESR of $\sim 5m\Omega$ for parallel total of $44\mu F$ and $2.5m\Omega$ ESR.

$$V_{RIPPLE,ESR} = 5.45A \times 2.5m\Omega = 13.6mV$$

$$V_{RIPPLE,CAP} = \frac{5.45A}{8 \times 44\mu F \times 600kHz} = 25.8mV$$

Total ripple = $39.4mV$. The actual capacitive ripple may be higher than calculated value because the capacitance decreases with the voltage on the capacitor.

Using a $150\mu F$ $40m\Omega$ POS cap, the above result is

$$V_{RIPPLE,ESR} = 5.45A \times 40m\Omega = 218mV$$

$$V_{RIPPLE,CAP} = \frac{5.45A}{8 \times 150\mu F \times 600kHz} = 7.56mV$$

Total ripple = $225mV$

Output Transient Undershoot/Overshoot

If very fast load transient must be supported, consider the effect of the output capacitor on the output transient undershoot and overshoot. Instant-PWM responds quickly to changing load conditions, however, some considerations must be needed, especially when using small ceramic capacitors which have low capacitance at low output voltages which results in insufficient stored energy for load transient. Output transient undershoot and overshoot have two causes: voltage changes caused by the ESR of the output capacitor and voltage changes caused by the output capacitance and inductor current slew rate.

ESR undershoot or overshoot may be calculated as $V_{ESR} = \Delta I_{OUT} \times ESR$. Using the ceramic capacitor example above and a fast load transient of $\pm 6A$, $V_{ESR} = \pm 6A \times 2.5m\Omega = \pm 15mV$. The POS capacitor result with the same load transient, $V_{ESR} = \pm 6A \times 40m\Omega = \pm 240mV$.

Capacitive undershoot (load increasing) is a function of the output capacitance, the load step, the inductor value and the input-output voltage difference and the maximum duty factor. During a fast load transient, the maximum duty factor of instant-PWM is a function of t_{ON} and the minimum t_{OFF} as the control scheme is designed to rapidly ramp the inductor current by grouping together many t_{ON} pulses in this case. The maximum duty factor D_{MAX} may be calculated by

$$D_{MAX} = \frac{t_{ON}}{t_{ON} + t_{OFF,MIN}}$$



Given this, the capacitive undershoot may be calculated by

$$V_{\text{UNDERSHOOT,CAP}} = -\frac{L_1 \times \Delta I_{\text{OUT}}^2}{2 \times C_{\text{OUT}} \times (V_{\text{IN,MIN}} \times D_{\text{MAX}} - V_{\text{OUT}})}$$

Consider a 6A load increase using the ceramic capacitor case when $V_{\text{IN}} = 12\text{V}$. At $V_{\text{OUT}} = 1.2\text{V}$, the result is $t_{\text{ON}} = 167\text{ns}$, $t_{\text{OFF,MIN}} = 150\text{ns}$, $D_{\text{MAX}} = 167 / (167 + 150) = 0.526$ and

$$V_{\text{UNDERSHOOT,CAP}} = -\frac{0.33\mu\text{H} \times (6\text{A})^2}{2 \times 44\mu\text{F} \times (12\text{V} \times 0.526 - 1.2\text{V})} = -26.4\text{mV}$$

Using the POS capacitor case, the above result is

$$V_{\text{UNDERSHOOT,CAP}} = -\frac{0.33\mu\text{H} \times (6\text{A})^2}{2 \times 150\mu\text{F} \times (12\text{V} \times 0.526 - 1.2\text{V})} = -7.7\text{mV}$$

Capacitive overshoot (load decreasing) is a function of the output capacitance, the inductor value and the output voltage.

$$V_{\text{OVERSHOOT,CAP}} = \frac{L_1 \times \Delta I_{\text{OUT}}^2}{2 \times C_{\text{OUT}} \times V_{\text{OUT}}}$$

Consider a 6A load decrease using the ceramic capacitor case above. At $V_{\text{OUT}} = 1.2\text{V}$ the result is

$$V_{\text{OVERSHOOT,CAP}} = \frac{0.33\mu\text{H} \times (6\text{A})^2}{2 \times 44\mu\text{F} \times 1.2\text{V}} = 112.5\text{mV}$$

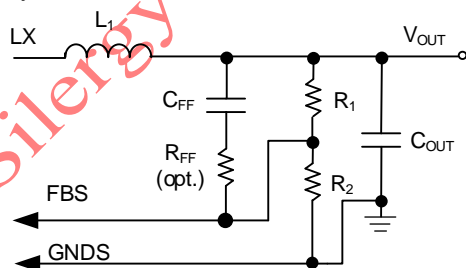
Using the POS capacitor case, the above result is

$$V_{\text{OVERSHOOT,CAP}} = \frac{0.33\mu\text{H} \times (6\text{A})^2}{2 \times 150\mu\text{F} \times 1.2\text{V}} = 33\text{mV}$$

Combine the ESR and capacitive undershoot and overshoot to calculate the total overshoot and undershoot for a given application.

Load Transient Considerations:

The SQ29012 adopts the instant PWM architecture to achieve good stability and fast transient responses. In applications with high step load current, adding an RC feed-forward compensation network R_{FF} and C_{FF} may further speed up the load transient responses. $R_{\text{FF}} = 1\text{k}\Omega$ and $C_{\text{FF}} = 220\text{pF}$ have been shown to perform well in most applications. Increase C_{FF} will speed up the load transient response if there is no stability issue.



Note that when $C_{\text{OUT}} > 500\mu\text{F}$ and minimum load current is low, set feed-forward values as $R_{\text{FF}} = 1\text{k}\Omega$ and $C_{\text{FF}} > 2.2\text{nF}$ to provide sufficient ripple to FB for small output ripple and good transient behavior.

Thermal Design Considerations

Maximum power dissipation depends on the thermal resistance of the IC package, the PCB layout, the surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation may be calculated by:

$$P_{\text{D,MAX}} = (T_{\text{J,MAX}} - T_{\text{A}}) / \theta_{\text{JA}}$$

Where, $T_{\text{J,MAX}}$ is the maximum junction temperature, T_{A} is the ambient temperature, and θ_{JA} is the junction to ambient thermal resistance.

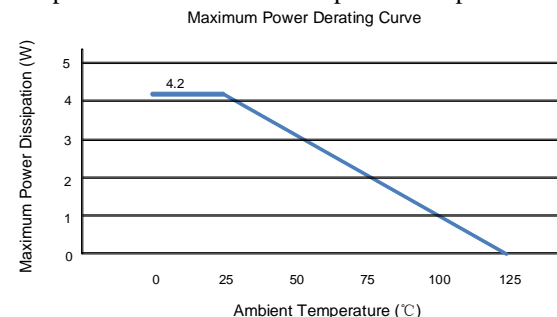
To comply with the recommended operating conditions, the maximum junction temperature is 125°C . The junction to ambient thermal resistance θ_{JA} is layout dependent. For the QFN3x4-19(FC) package the thermal resistance θ_{JA} is 24°C/W when measured on a standard Silergy four-layer thermal test board. These standard thermal test layouts have a very large area with long 2oz. copper traces connected to each IC pin and very large, unbroken 1oz. internal power and ground planes.

Meeting the performance of the standard thermal test board in a typical tiny evaluation board area requires wide copper traces well-connected to the IC's backside pads leading to exposed copper areas on the component side of the board as well as good thermal via from the exposed pad connecting to a wide middle-layer ground plane and, perhaps, to an exposed copper area on the board's solder side.

The maximum power dissipation at $T_{\text{A}} = 25^\circ\text{C}$ may be calculated by the following formula:

$$P_{\text{D,MAX}} = (125^\circ\text{C} - 25^\circ\text{C}) / (24^\circ\text{C/W}) = 4.2\text{W}$$

The maximum power dissipation depends on operating ambient temperature for fixed $T_{\text{J,MAX}}$ and thermal resistance θ_{JA} . Use the derating curve in figure below to calculate the effect of rising ambient temperature on the maximum power dissipation.



Layout Design

Follow these PCB layout guidelines for optimal performance and thermal dissipation.

- Place the major MLCC capacitors (C_{IN} , C_{OUT} , C_{VCC}) on the same layer as the device.



- Place the input capacitor very near IN and GND, minimizing the loop formed by these connections. Avoid using direct vias connection in the power trace between the input capacitors and IN, GND to reduce parasitic inductance.
- Place one smaller package input MLCC capacitor at the reach out port of pin18. This capacitor can be connected with GND by vias.
- Place the VCC capacitor close to VCC using short, direct connections instead of vias connection to device GND pins.
- Make one Kelvin connection between AGND and GND at the C_{VCC} negative sides.
- Place the feedback components (R_1 , R_2 , R_{FF} and C_{FF}) as close to the FBS pin as possible. Avoid routing the remote output sense line and remote GND sense (GNDS) line near LX, BS or other high frequency signal as they are noise sensitive.
- Make the feedback sampling point Kelvin connect with C_{OUT} rather than the inductor output terminal.
- Guarantee the C_{OUT} negative sides are connected with GND pin by wide copper traces instead of vias, in order to achieve better accuracy and stability of output voltage.
- The LX connection has large voltage swings and fast edges and can easily radiate noise to adjacent components. Keep its area small to prevent excessive EMI, while providing wide copper traces to minimize parasitic resistance and inductance. Keep sensitive components away from the switching node or provide ground traces between for shielding, to prevent stray capacitive noise pickup.
- Place the BS capacitor on the same layer as the device; keep the BS voltage path (BS, LX and C_{BS}) as short as possible.
- It is not recommended to connect control signals and IN directly. A resistor in a range of $1k\Omega$ to $1M\Omega$ should be used if they are pulled high by IN.
- Provide dedicated wide copper traces for the power path ground between the IC and the input and output capacitor grounds, rather than connecting each of these individually to an internal ground plane.
- The exposed GND pad should be connected to a large copper area and place several GND vias on it for heat sinking and to minimize noise.
- A four-layer layout is strongly recommended to achieve better thermal performance. $8.5cm \times 8.5cm$, four-layer PCB with 2-oz copper used as example.
- Keep the high current traces (IN, GND, LX and OUT traces) as short and wide as possible.
- The top layer and bottom layer should place power IN and GND copper plane as wide as possible. Middle1 layer should place all GND layer for conducting heat and shielding middle2 layer signal line from top layer crosstalk. Place signal lines on middle2 layer instead of other layers to avoid top and bottom GND layer be cut apart.

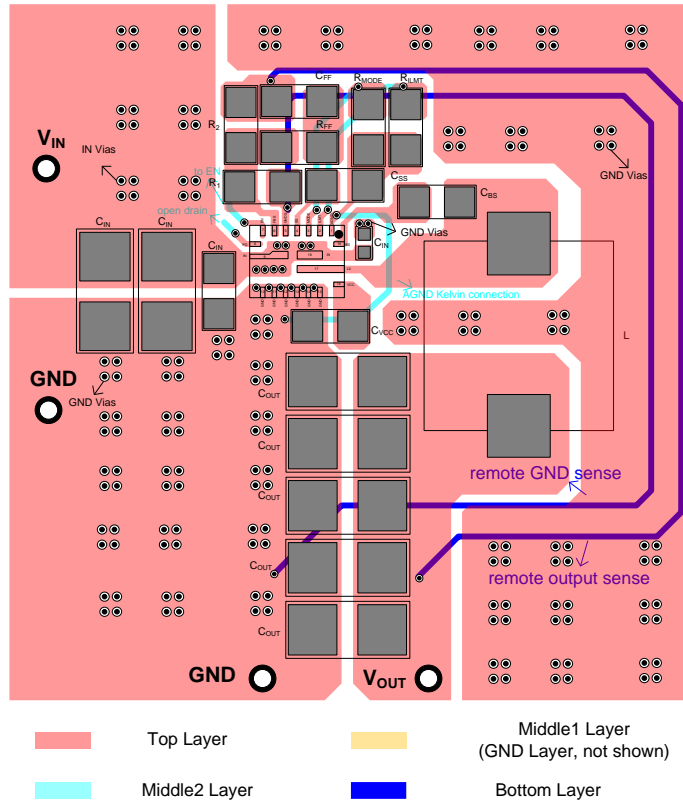
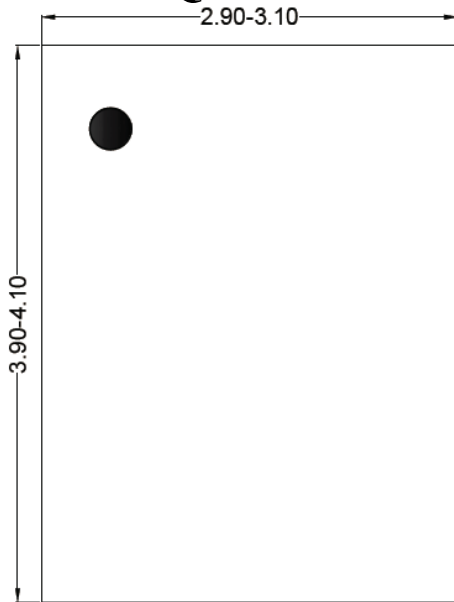
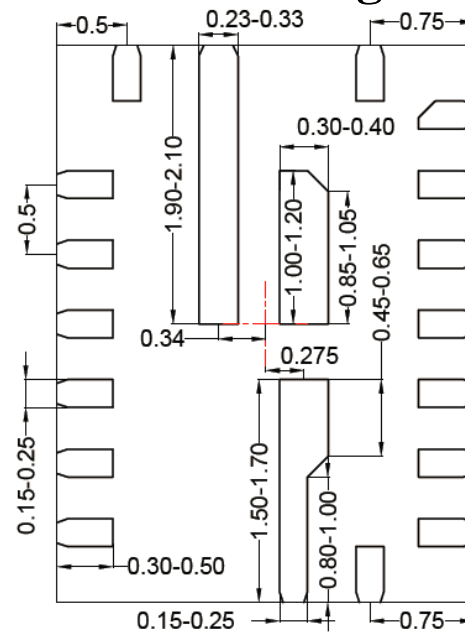


Figure4. PCB Layout Suggestion

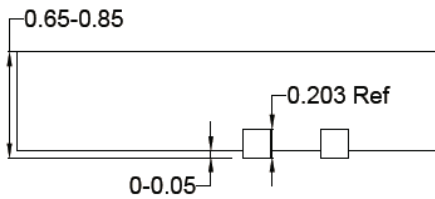
QFN3×4-19 Package Outline Drawing



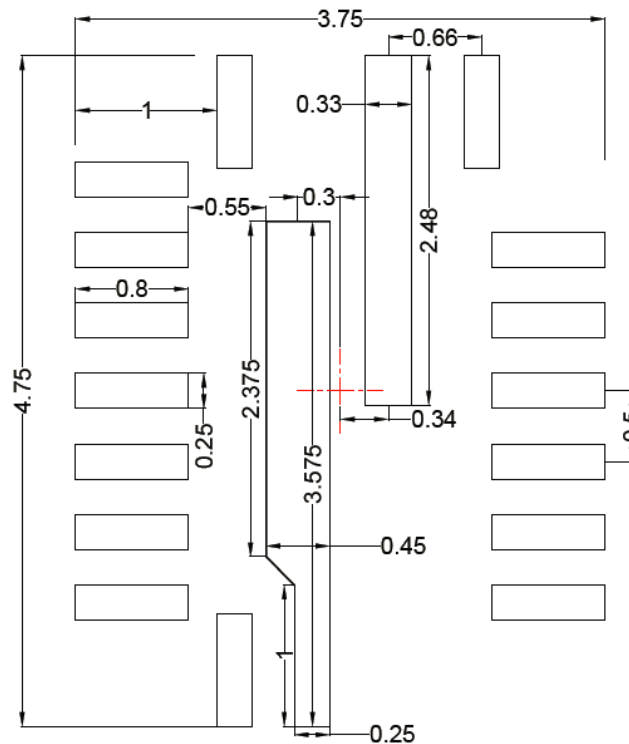
Top view



Bottom view



Front view

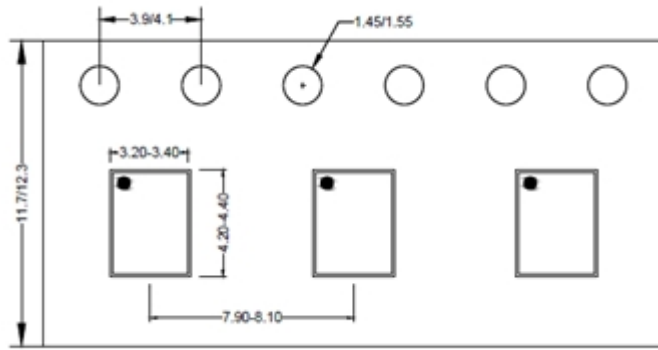


Recommended PCB layout
(Reference only)

**Notes: 1, All dimension in millimeter and exclude mold flash & metal burr.
2, center line refers chip body center.**

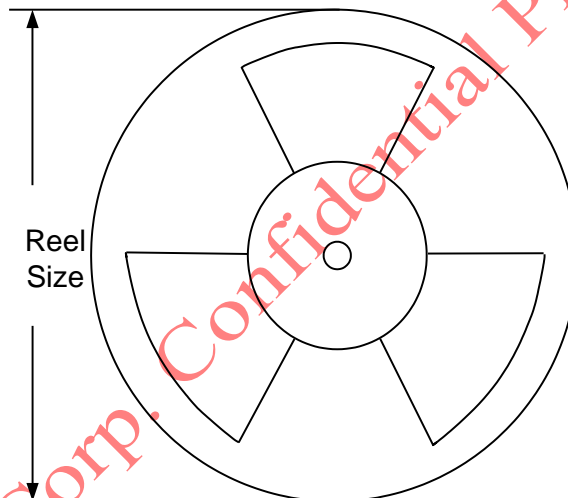
Taping & Reel Specification

1. Taping orientation for packages



Feeding direction →

2. Carrier Tape & Reel specification for packages



Package type	Tape width (mm)	Pocket pitch(mm)	Reel size (Inch)	Trailer length(mm)	Leader length (mm)	Qty per reel
QFN3×4	12	8	13"	400	400	5000

3. Others: NA